

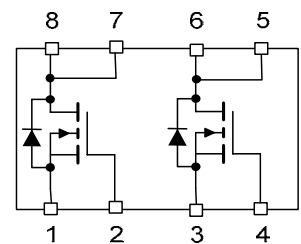
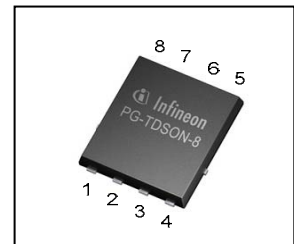
**OptiMOS<sup>®</sup> Power-Transistor**

**Features**

- Dual N-channel Logic Level - Enhancement mode
- AEC Q101 qualified
- MSL1 up to 260°C peak reflow
- 175°C operating temperature
- Green Product (RoHS compliant)
- 100% Avalanche tested

**Product Summary**

|                       |    |    |
|-----------------------|----|----|
| $V_{DS}$              | 55 | V  |
| $R_{DS(on),max}^{4)}$ | 50 | mΩ |
| $I_D$                 | 20 | A  |

**PG-TDSON-8-4**


| Type           | Package      | Marking |
|----------------|--------------|---------|
| IPG20N06S2L-50 | PG-TDSON-8-4 | 2N06L50 |

**Maximum ratings, at  $T_j=25\text{ °C}$ , unless otherwise specified**

| Parameter  | Symbol         | Conditions                                     | Value        | Unit |
|--|----------------|--|--------------|------|
| Continuous drain current<br>one channel active <sup>2)</sup> | $I_D$          | $T_C=25\text{ °C}$ , $V_{GS}=10\text{ V}^{1)}$ | 20           | A    |
|  |                | $T_C=100\text{ °C}$ , $V_{GS}=10\text{ V}$     | 16           |      |
| Pulsed drain current <sup>2)</sup><br>one channel active     | $I_{D,pulse}$  | -  | 80           |      |
| Avalanche energy, single pulse <sup>2, 4)</sup>              | $E_{AS}$       | $I_D=10\text{ A}$                              | 60           | mJ   |
| Avalanche current, single pulse <sup>4)</sup>                | $I_{AS}$       | -  | 15           | A    |
| Gate source voltage  | $V_{GS}$       | -  | ±20          | V    |
| Power dissipation<br>one channel active                      | $P_{tot}$      | $T_C=25\text{ °C}$                             | 51           | W    |
| Operating and storage temperature                            | $T_j, T_{stg}$ | -  | -55 ... +175 | °C   |
| IEC climatic category; DIN IEC 68-1                          | -              | -  | 55/175/56    |      |

| Parameter                                   | Symbol     | Conditions                                   | Values |      |      | Unit |
|---|------------|--|--------|------|------|------|
|   |            |  | min.   | typ. | max. |      |
| <b>Thermal characteristics<sup>2)</sup></b> |            |  |        |      |      |      |
| Thermal resistance, junction - case         | $R_{thJC}$ | -  | -      | -    | 2.9  | K/W  |
| SMD version, device on PCB                  | $R_{thJA}$ | minimal footprint                            | -      | 100  | -    |      |
|   |            | 6 cm <sup>2</sup> cooling area <sup>3)</sup> | -      | 60   | -    |      |

**Electrical characteristics, at  $T_j=25\text{ °C}$ , unless otherwise specified**

**Static characteristics**

|  |               |   |     |      |     |               |
|--|---------------|---|-----|------|-----|---------------|
| Drain-source breakdown voltage                 | $V_{(BR)DSS}$ | $V_{GS}=0\text{ V}, I_D=1\text{ mA}$                            | 55  | -    | -   | V             |
| Gate threshold voltage                         | $V_{GS(th)}$  | $V_{DS}=V_{GS}, I_D=19\text{ }\mu\text{A}$                      | 1.2 | 1.6  | 2.0 |               |
| Zero gate voltage drain current <sup>4)</sup>  | $I_{DSS}$     | $V_{DS}=55\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ °C}$       | -   | 0.01 | 1   | $\mu\text{A}$ |
|  |               | $V_{DS}=55\text{ V}, V_{GS}=0\text{ V}, T_j=125\text{ °C}^{2)}$ | -   | 1    | 100 |               |
| Gate-source leakage current <sup>4)</sup>      | $I_{GSS}$     | $V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$                         | -   | 1    | 100 | nA            |
| Drain-source on-state resistance <sup>4)</sup> | $R_{DS(on)}$  | $V_{GS}=4.5\text{ V}, I_D=10\text{ A}$                          | -   | 50   | 60  | m $\Omega$    |
|  |               | $V_{GS}=10\text{ V}, I_D=15\text{ A}$                           | -   | 39   | 50  |               |

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

**Dynamic characteristics<sup>2)</sup>**

|  |              |   |   |     |     |    |
|--|--------------|---|---|-----|-----|----|
| Input capacitance <sup>4)</sup>            | $C_{iss}$    | $V_{GS}=0\text{ V}, V_{DS}=25\text{ V},$<br>$f=1\text{ MHz}$                          | - | 430 | 560 | pF |
| Output capacitance <sup>4)</sup>           | $C_{oss}$    |   | - | 120 | 160 |    |
| Reverse transfer capacitance <sup>4)</sup> | $C_{rss}$    |   | - | 45  | 68  |    |
| Turn-on delay time                         | $t_{d(on)}$  | $V_{DD}=27.5\text{ V},$<br>$V_{GS}=10\text{ V}, I_D=20\text{ A},$<br>$R_G=11\ \Omega$ | - | 2   | -   | ns |
| Rise time                                  | $t_r$        |   | - | 3   | -   |    |
| Turn-off delay time                        | $t_{d(off)}$ |   | - | 15  | -   |    |
| Fall time                                  | $t_f$        |   | - | 10  | -   |    |

**Gate Charge Characteristics<sup>2, 4)</sup>**

|                       |               |  |   |     |     |    |
|-----------------------|---------------|--|---|-----|-----|----|
| Gate to source charge | $Q_{gs}$      | $V_{DD}=44\text{ V}, I_D=20\text{ A},$<br>$V_{GS}=0\text{ to }10\text{ V}$ | - | 1.5 | 2   | nC |
| Gate to drain charge  | $Q_{gd}$      |  | - | 4.6 | 6.9 |    |
| Gate charge total     | $Q_g$         |  | - | 13  | 17  |    |
| Gate plateau voltage  | $V_{plateau}$ |  | - | 3.7 | -   | V  |

**Reverse Diode**

|  |               |   |   |     |     |    |
|--|---------------|---|---|-----|-----|----|
| Diode continuous forward current <sup>2)</sup><br>one channel active | $I_S$         | $T_C=25\text{ }^\circ\text{C}$  | - | -   | 20  | A  |
| Diode pulse current <sup>2)</sup><br>one channel active              | $I_{S,pulse}$ |   | - | -   | 80  |    |
| Diode forward voltage  | $V_{SD}$      | $V_{GS}=0\text{ V}, I_F=15\text{ A},$<br>$T_j=25\text{ }^\circ\text{C}$ | - | 1.0 | 1.3 | V  |
| Reverse recovery time <sup>2)</sup>                                  | $t_{rr}$      | $V_R=27.5\text{ V}, I_F=I_S,$<br>$di_F/dt=100\text{ A}/\mu\text{s}$     | - | 25  | -   | ns |
| Reverse recovery charge <sup>2, 4)</sup>                             | $Q_{rr}$      |   | - | 24  | -   | nC |

<sup>1)</sup> Current is limited by bondwire; with an  $R_{thJC}=2.9\text{ K/W}$  the chip is able to carry 23A at 25°C.

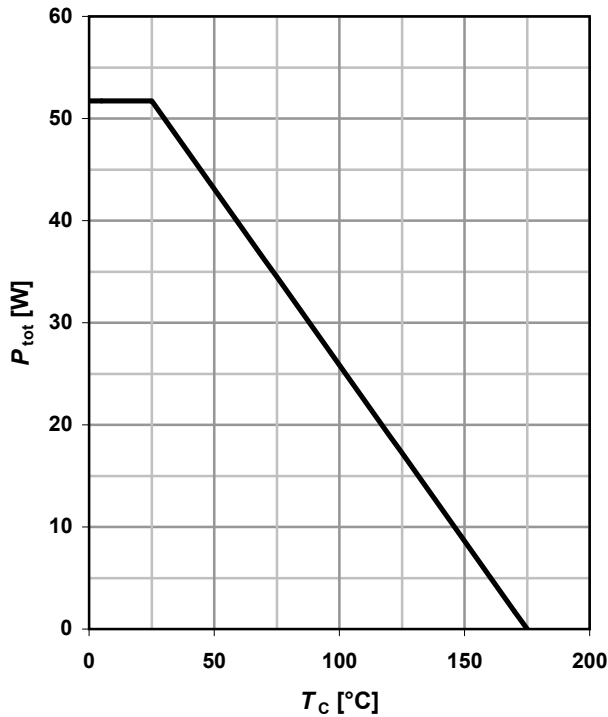
<sup>2)</sup> Specified by design. Not subject to production test.

<sup>3)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70 μm thick) copper area for drain connection. PCB is vertical in still air.

<sup>4)</sup> Per channel

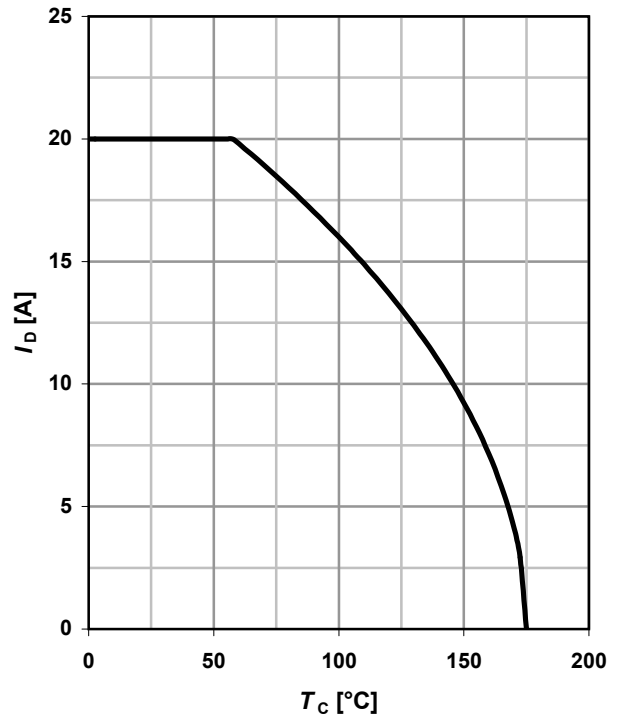
**1 Power dissipation**

$P_{tot} = f(T_C)$ ;  $V_{GS} \geq 6\text{ V}$ ; one channel active



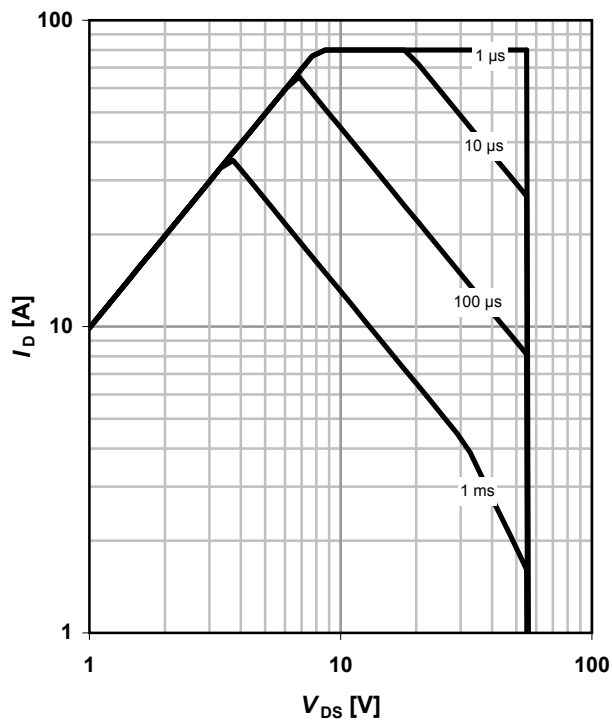
**2 Drain current**

$I_D = f(T_C)$ ;  $V_{GS} \geq 6\text{ V}$ ; one channel active



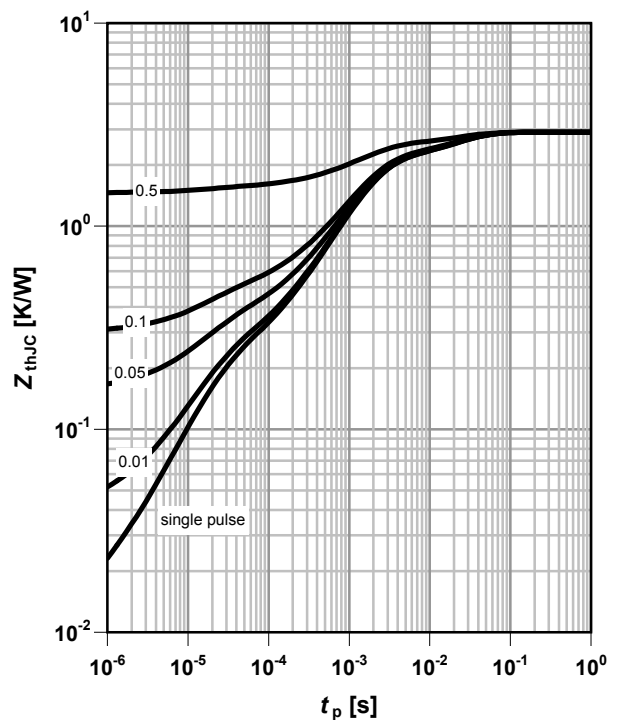
**3 Safe operating area**

$I_D = f(V_{DS})$ ;  $T_C = 25^\circ\text{C}$ ;  $D = 0$ ; one channel active  
parameter:  $t_p$



**4 Max. transient thermal impedance**

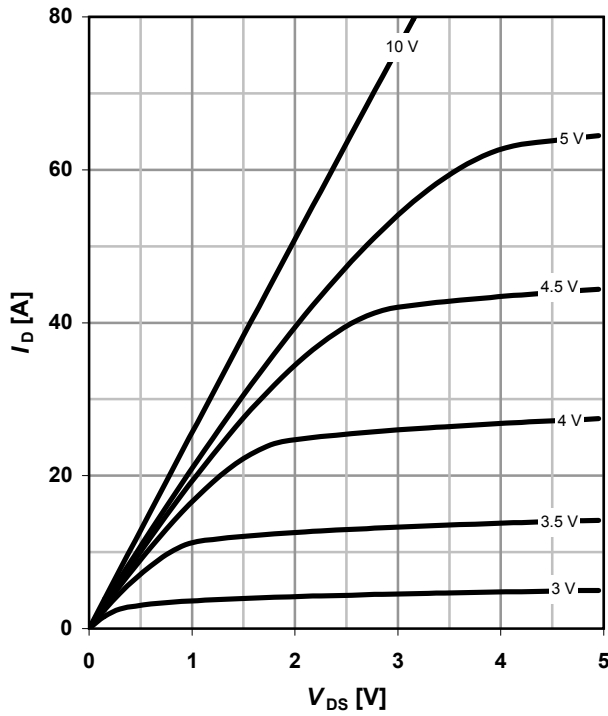
$Z_{thJC} = f(t_p)$   
parameter:  $D = t_p/T$



**5 Typ. output characteristics<sup>4)</sup>**

$I_D = f(V_{DS}); T_j = 25\text{ }^\circ\text{C}$

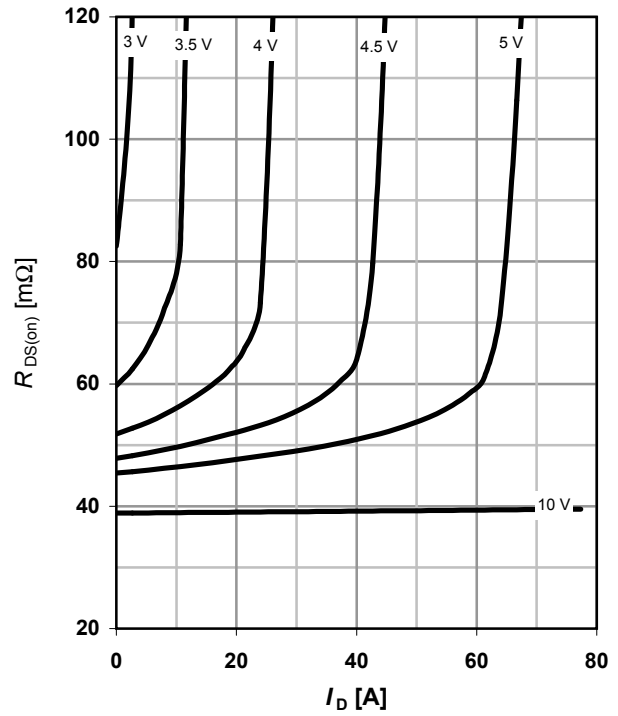
parameter:  $V_{GS}$



**6 Typ. drain-source on-state resistance<sup>4)</sup>**

$R_{DS(on)} = f(I_D); T_j = 25\text{ }^\circ\text{C}$

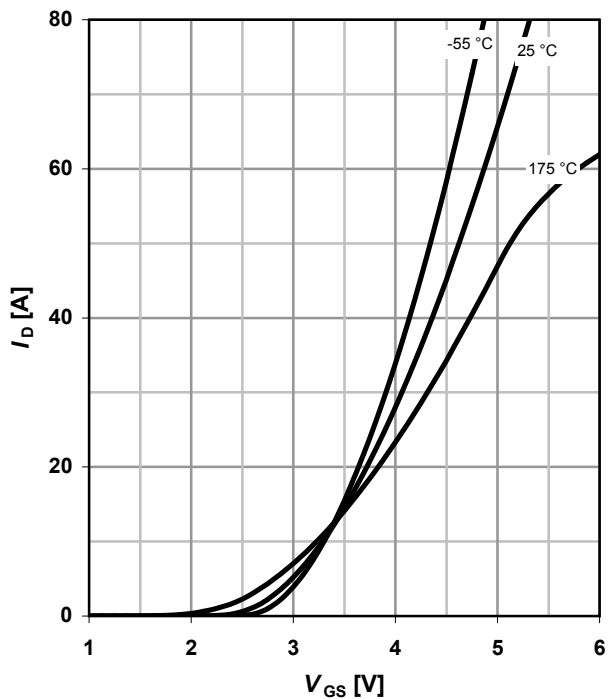
parameter:  $V_{GS}$



**7 Typ. transfer characteristics<sup>4)</sup>**

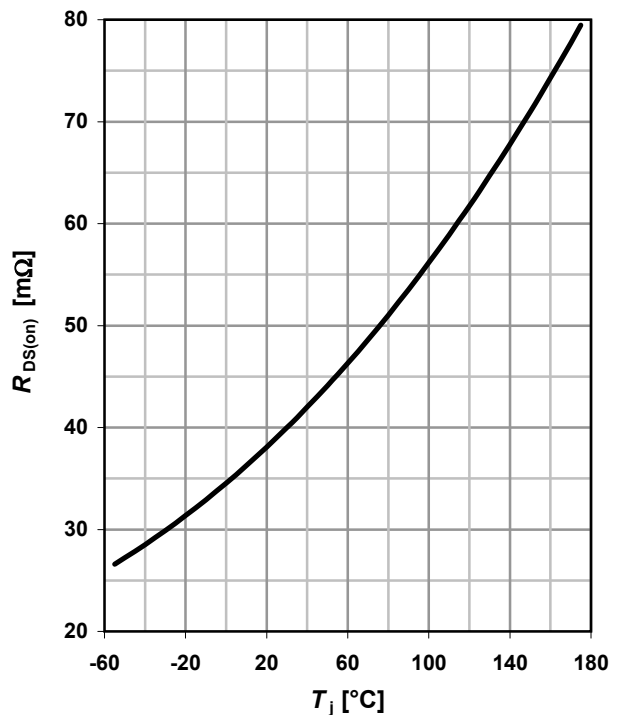
$I_D = f(V_{GS}); V_{DS} = 6\text{ V}$

parameter:  $T_j$



**8 Typ. drain-source on-state resistance<sup>4)</sup>**

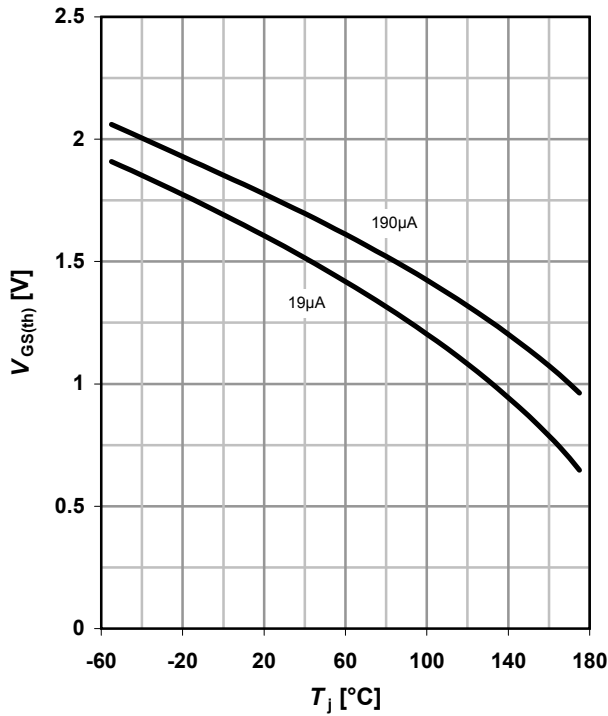
$R_{DS(on)} = f(T_j); I_D = 15\text{ A}; V_{GS} = 10\text{ V}$



**9 Typ. gate threshold voltage**

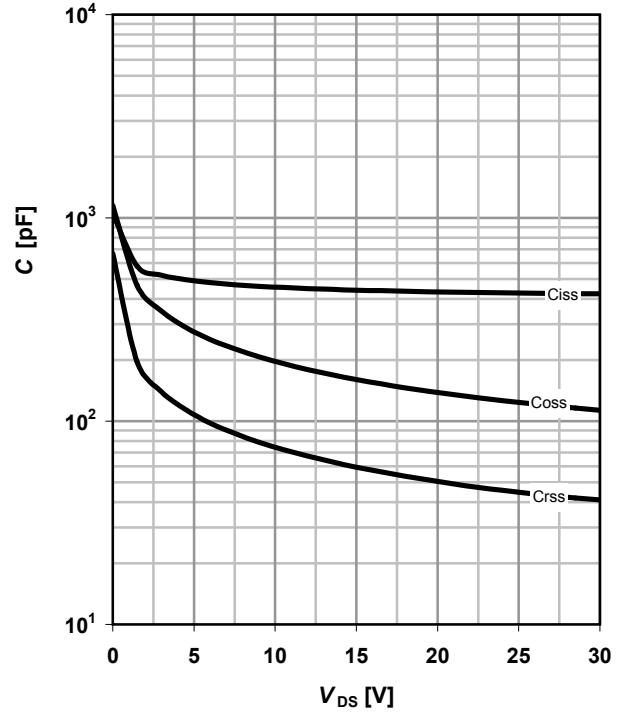
$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$

parameter:  $I_D$



**10 Typ. Capacitances<sup>4)</sup>**

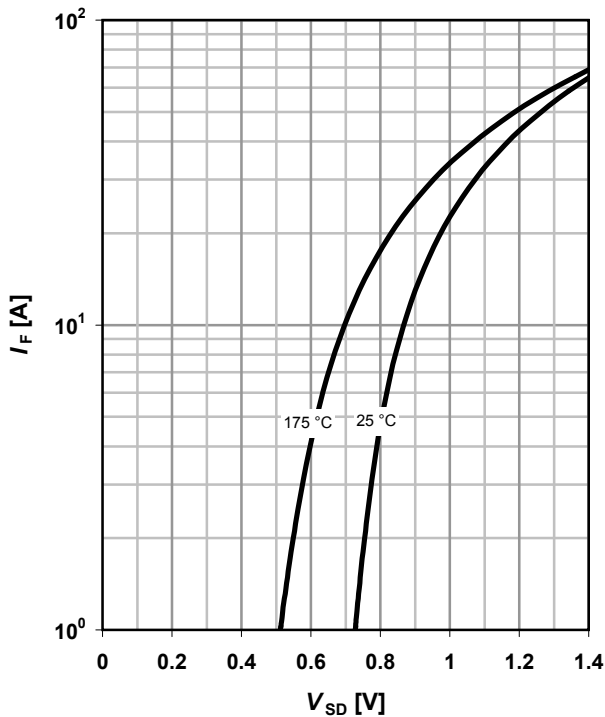
$C = f(V_{DS}); V_{GS} = 0 V; f = 1 MHz$



**11 Typical forward diode characteristics<sup>4)</sup>**

$I_F = f(V_{SD})$

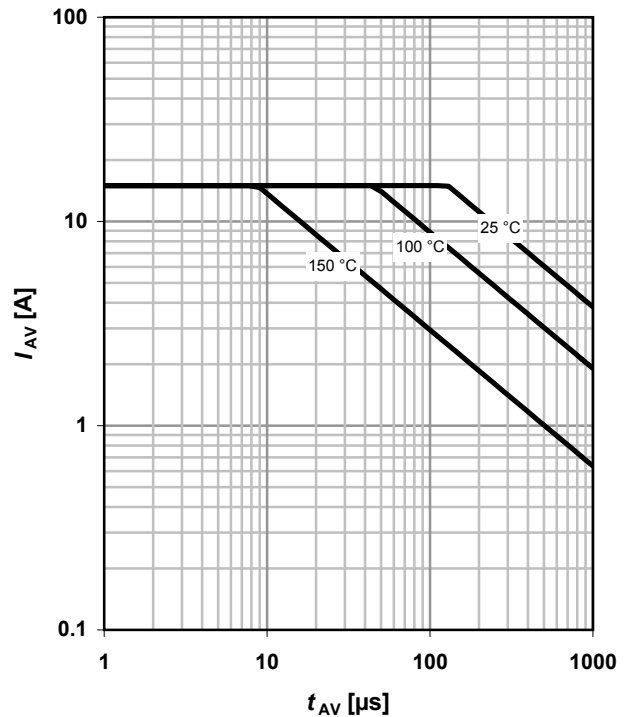
parameter:  $T_j$



**12 Avalanche characteristics<sup>4)</sup>**

$I_{AS} = f(t_{AV})$

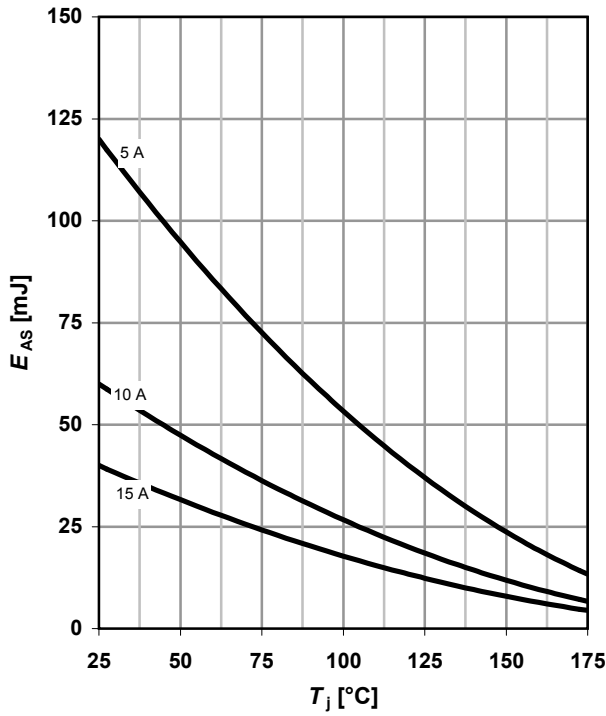
parameter:  $T_{j(start)}$



**13 Avalanche energy<sup>4)</sup>**

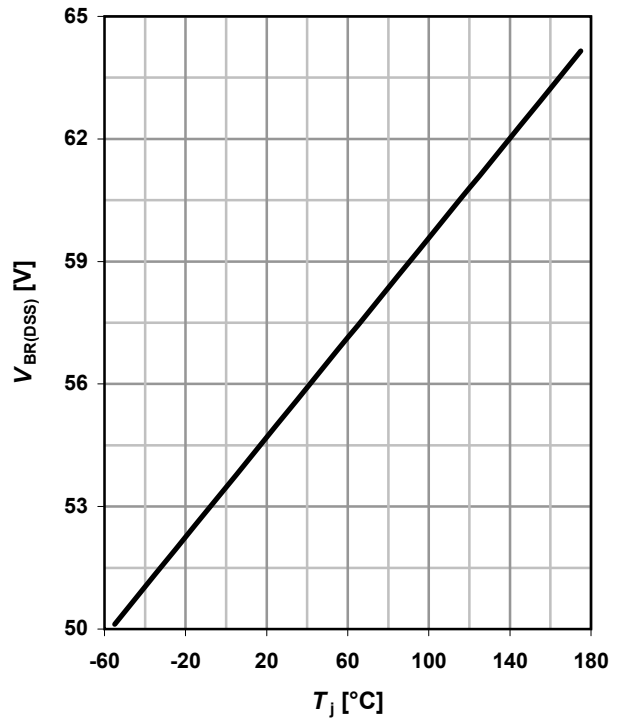
$E_{AS} = f(T_j)$

parameter:  $I_D$



**14 Drain-source breakdown voltage**

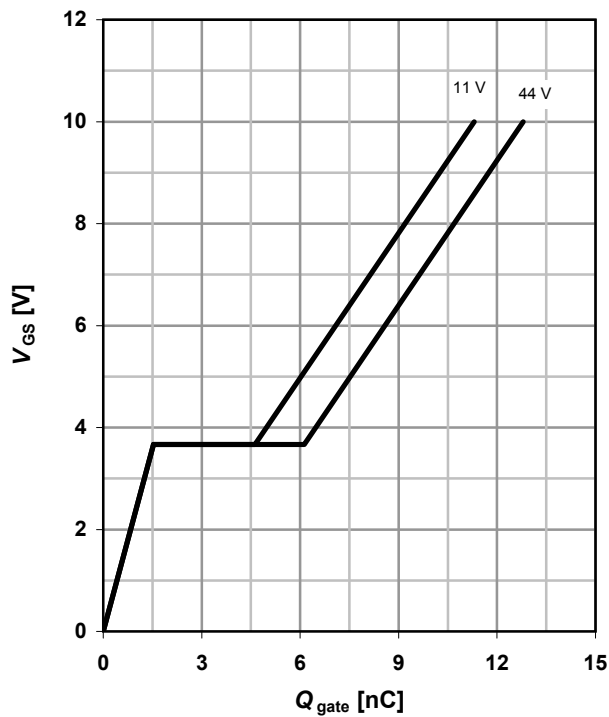
$V_{BR(DSS)} = f(T_j); I_D = 1 \text{ mA}$



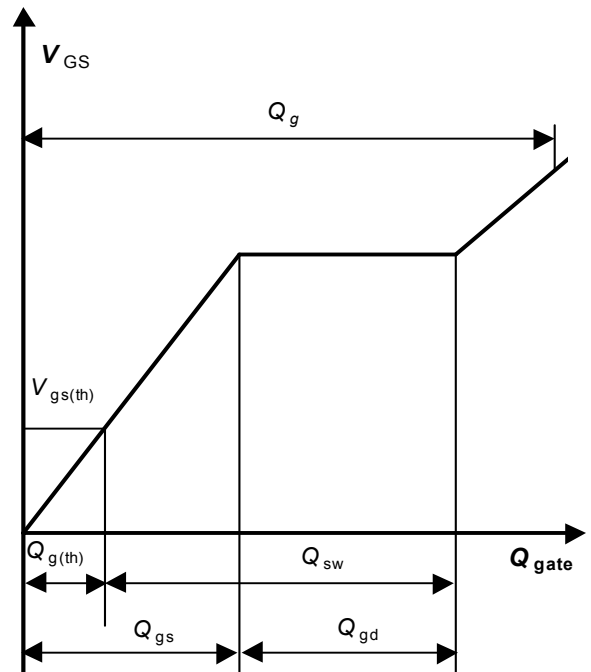
**15 Typ. gate charge<sup>4)</sup>**

$V_{GS} = f(Q_{gate}); I_D = 20 \text{ A pulsed}$

parameter:  $V_{DD}$



**16 Gate charge waveforms**



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## Revision History

| Version      | Date       | Changes          |
|--------------|------------|------------------|
| Revision 1.0 | 07.09.2009 | Final Data Sheet |
|              |            |                  |

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